

FORM PTO-1390 (Modified) U.S. PATENT AND TRADEMARK OFFICE; U.S. DEPARTMENT OF COMMERCE  
(REV. 12-2004)

**TRANSMITTAL LETTER TO THE UNITED STATES  
DESIGNATED/ELECTED OFFICE (DO/EO/US)  
CONCERNING A SUBMISSION UNDER 35 U.S.C. 371**

ATTORNEY'S DOCKET NUMBER

112857-534

U.S. APPLICATION NO. (If known, see 37 CFR 1.5)

10/512,131

INTERNATIONAL APPLICATION NO.  
PCT/JP04/001952INTERNATIONAL FILING DATE  
February 19, 2004PRIORITY DATE CLAIMED  
March 20, 2003

## TITLE OF INVENTION

**SEMICONDUCTOR LIGHT EMITTING ELEMENT, MANUFACTURING METHOD THEREOF, INTEGRATED  
SEMICONDUCTOR LIGHT EMITTING DEVICE, MANUFACTURING METHOD THEREOF, IMAGE DISPLAY DEVICE...**

APPLICANT(S) FOR DO/EO/US

Okuyama et al.

Applicant herewith submits to the United States Designated/Elected Office (DO/EO/US) the following items and other information:

1. ☐ This is a **FIRST** submission of items concerning a submission under 35 U.S.C. 371.
2. ☒ This is a **SECOND** or **SUBSEQUENT** submission of items concerning a submission under 35 U.S.C. 371.
3. ☐ This is an express request to begin national examination procedures (35 U.S.C. 371(f)). The submission must include items (5), (6), (9) and (24) indicated below.
4. ☐ The US has been elected (Article 31).
5. ☐ A copy of the International Application as filed (35 U.S.C. 371 (c)(2))
  - a. ☐ is attached hereto (required only if not communicated by the International Bureau).
  - b. ☐ has been communicated by the International Bureau.
  - c. ☐ is not required, as the application was filed in the United States Receiving Office (RO/US).
6. ☐ An English language translation of the International Application as filed (35 U.S.C. 371(c)(2)).
  - a. ☐ is attached hereto.
  - b. ☐ has been previously submitted under 35 U.S.C. 154(d)(4).
7. ☐ Amendments to the claims of the International Application under PCT Article 19 (35 U.S.C. 371 (c)(3))
  - a. ☐ are attached hereto (required only if not communicated by the International Bureau).
  - b. ☐ have been communicated by the International Bureau.
  - c. ☐ have not been made; however, the time limit for making such amendments has NOT expired.
  - d. ☐ have not been made and will not be made.
8. ☐ An English language translation of the amendments to the claims under PCT Article 19 (35 U.S.C. 371(c)(3)).
9. ☐ An oath or declaration of the inventor(s) (35 U.S.C. 371 (c)(4)).
10. ☐ An English language translation of the annexes to the International Preliminary Examination Report under PCT Article 36 (35 U.S.C. 371 (c)(5)).
11. ☐ A copy of the International Preliminary Examination Report (PCT/IPEA/409).
12. ☐ A copy of the International Search Report (PCT/ISA/210).

**Items 13 to 23 below concern document(s) or information included:**

13. ☒ An Information Disclosure Statement under 37 CFR 1.97 and 1.98.
14. ☐ An assignment document for recording. A separate cover sheet in compliance with 37 CFR 3.28 and 3.31 is included.
15. ☐ A **FIRST** preliminary amendment.
16. ☐ A **SECOND** or **SUBSEQUENT** preliminary amendment.
17. ☐ A substitute specification.
18. ☐ A power of attorney and/or change of address letter.
19. ☐ A computer-readable form of the sequence listing in accordance with PCT Rule 13ter.2 and 37 CFR 1.821 - 1.825.
20. ☐ A second copy of the published International Application under 35 U.S.C. 154(d)(4).
21. ☐ A second copy of the English language translation of the International Application under 35 U.S.C. 154(d)(4).
22. ☒ Express Mail Label No. EV 351195750 US
23. ☒ Other items or information:

Return Receipt Postcard.

Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it displays a valid OMB control number.

|  |              |  |   |   |            |
|--|--------------|--|---|---|------------|
| U.S. APPLICATION NO (if known, see 37 CFR 1.5)<br><b>10/512,131</b>  |              | INTERNATIONAL APPLICATION NO.<br><b>PCT/JP04/001952</b>                |   | ATTORNEY'S DOCKET NUMBER<br><b>112857-534</b> |            |
| 24. The following fees are submitted:  |              |  |   | Applicant use                                 | Office use |
| <input type="checkbox"/> a) Basic national fee ..... \$300.00  |              |  |   | \$  | \$0.00     |
| <input type="checkbox"/> b) Examination fee ..... \$200.00   |              |  |   | \$  | \$0.00     |
| <input type="checkbox"/> c) Search fee ..... \$500.00  |              |  |   | \$  | \$0.00     |
| <b>TOTAL OF ABOVE CALCULATIONS =</b> \$1000.00   |              |  |   | \$  | \$0.00     |
| <input type="checkbox"/> Additional fee for specification and drawings filed in paper over 100 sheets (excluding sequence listing or computer program listing filed in an electronic medium). The fee is \$250 for each additional 50 sheets of paper or fraction thereof.   |              |  |   |   |            |
| Total Sheets   | Extra Sheets | Number of each additional 50 or fraction thereof (round up to a whole) | RATE  |   |            |
| - 100 =  | /50 =        |  | x \$250.00  | \$  | \$0.00     |
| Surcharge of \$130.00 for furnishing the oath or declaration later than months from the earliest claimed priority date (37 CFR 1.492(e)).  |              |  |   | \$  |            |
| CLAIMS   | NUMBER FILED | NUMBER EXTRA   | RATE  |   |            |
| Total claims   | - 20 =       | 0  | x \$50.00   | \$  | \$0.00     |
| Independent claims   | - 3 =        | 0  | x \$200.00  | \$  | \$0.00     |
| MULTIPLE DEPENDENT CLAIMS (if applicable) <input type="checkbox"/> + \$360.00  |              |  |   | \$  | \$0.00     |
| <b>TOTAL OF ABOVE CALCULATIONS =</b>   |              |  |   | \$  | \$0.00     |
| <input type="checkbox"/> Applicant claims small entity status. See 37 CFR 1.27. The fees indicated above are reduced by 1/2.   |              |  |   | \$  | \$0.00     |
| <b>SUBTOTAL =</b>  |              |  |   | \$  | \$0.00     |
| Processing fee of \$130.00 for furnishing the English translation later than 30 months from the earliest claimed priority date (37 CFR 1.492(f)).  |              |  |   | \$  | \$0.00     |
| <b>TOTAL NATIONAL FEE =</b>  |              |  |   | \$  | \$0.00     |
| Fee for recording the enclosed assignment (37 CFR 1.21(h)). The assignment must be accompanied by an appropriate cover sheet (37 CFR 3.28, 3.31). \$40 per property +  |              |  |   | \$  | \$0.00     |
| <b>TOTAL FEES ENCLOSED =</b>   |              |  |   | \$  | \$0.00     |
| <b>Amount to be refunded:</b>  |              |  |   |   | \$         |
| <b>Amount to be charged:</b>   |              |  |   |   | \$         |
| <p>a. <input type="checkbox"/> A check in the amount of \$ _____ to cover the above fees is enclosed.</p> <p>b. <input type="checkbox"/> Please charge my Deposit Account No. _____ in the amount of _____ to cover the above fees. A duplicate copy of this sheet is _____</p> <p>c. <input checked="" type="checkbox"/> The Director is hereby authorized to charge any additional fees which may be required, or credit any overpayment to Deposit Account No. <u>02-1818</u>. A duplicate copy of this sheet is enclosed.</p> <p>d. <input type="checkbox"/> Fees are to be charged to a credit card. <b>WARNING:</b> Information on this form may become public. <b>Credit card information should not be included on this form.</b> Provide credit card information and authorization on PTO-2038.</p> |              |  |   |   |            |
| <p><b>NOTE:</b> Where an appropriate time limit under 37 CFR 1.495 has not been met, a petition to revive (37 CFR 1.137(a) or (b)) must be filed and granted to restore the International Application to pending status.</p>   |              |  |   |   |            |
| SEND ALL CORRESPONDENCE TO:  |              |  |   |   |            |
| Thomas C. Basso<br>BELL, BOYD & LLOYD LLC<br>P.O. Box 1135<br>Chicago, Illinois 60690-1135   |              |  | SIGNATURE<br>Thomas C. Basso<br>NAME<br>46,541<br>REGISTRATION NUMBER |   |            |

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Okuyama et al.  
Appl. No.: 10/512,131  
Intl. Appl. No.: PCT/JP04/001952  
Conf. No.: Unknown  
Filed: October 21, 2004  
Title: SEMICONDUCTOR LIGHT EMITTING ELEMENT, MANUFACTURING  
METHOD THEREOF, INTEGRATED SEMICONDUCTOR LIGHT  
EMITTING DEVICE, MANUFACTURING METHOD THEREOF, IMAGE  
DISPLAY DEVICE, MANUFACTURING METHOD THEREOF,  
ILLUMINATING DEVICE AND MANUFACTURING METHOD  
THEREOF  
Art Unit: Unknown  
Examiner: Unknown  
Docket No.: 112857-534

Mail Stop PCT  
Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

**CERTIFICATE OF MAILING BY EXPRESS MAIL UNDER 37 CFR 1.10**

Sir:

I hereby certify that the following documents relating to the above-identified application:

1. Transmittal Letter to the U.S. Designated/Elected Office (DO/EO/US) (Duplicate);
2. Transmittal of Information Disclosure Statement (Duplicate);
3. Supplemental Information Disclosure Statement (3 Pages);
4. PTO Form 1449 (2 Pages);
5. Cited References (40 References); and
6. Return Receipt Postcard

are being deposited with the United States Postal Service with sufficient postage as Express Mail  
in an envelope addressed to:

Mail Stop  
Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

on February 18, 2005.

Respectfully submitted,

BELL, BOYD & LLOYD LLC

Heather Foster

Name of Person Mailing Correspondence



Signature

EV 351195750 US

Express Mail Mailing Label Number

**TRANSMITTAL OF INFORMATION DISCLOSURE STATEMENT**  
**(Under 37 CFR 1.97(b) or 1.97(c))**

Docket No.  
112857-534

In Re Application Of: **Okuyama et al.**

| Application No. | Filing Date | Examiner | Customer No. | Group Art Unit | Confirmation No. |
|-----------------|-------------|----------|--------------|----------------|------------------|
| 10/512,131      | 10/21/2004  | Unknown  | 29175        | Unknown        | Unknown          |

Title: **SEMICONDUCTOR LIGHT EMITTING ELEMENT, MANUFACTURING METHOD THEREOF, INTEGRATED SEMICONDUCTOR LIGHT EMITTING DEVICE, MANUFACTURING METHOD THEREOF, IMAGE DISPLAY DEVICE, MANUFACTURING METHOD THEREOF, ILLUMINATING DEVICE AND MANUFACTURING METHOD THEREOF**

Address to:  
**Commissioner for Patents**  
**P.O. Box 1450**  
**Alexandria, VA 22313-1450**

**37 CFR 1.97(b)**

1. ☒ The Information Disclosure Statement submitted herewith is being filed within three months of the filing of a national application other than a continued prosecution application under 37 CFR 1.53(d); within three months of the date of entry of the national stage as set forth in 37 CFR 1.491 in an international application; before the mailing of a first Office Action on the merits, or before the mailing of a first Office Action after the filing of a request for continued examination under 37 CFR 1.114.

**37 CFR 1.97(c)**

2. ☐ The Information Disclosure Statement submitted herewith is being filed after the period specified in 37 CFR 1.97(b), provided that the Information Disclosure Statement is filed before the mailing date of a Final Action under 37 CFR 1.113, a Notice of Allowance under 37 CFR 1.311, or an Action that otherwise closes prosecution in the application, and is accompanied by one of:

☐ the statement specified in 37 CFR 1.97(e);

**OR**

☐ the fee set forth in 37 CFR 1.17(p).

**TRANSMITTAL OF INFORMATION DISCLOSURE STATEMENT**  
(Under 37 CFR 1.97(b) or 1.97(c))

Docket No.  
112857-534

In Re Application: **Okuyama et al.**

| Application No. | Filing Date | Examiner | Customer No. | Group Art Unit | Confirmation No. |
|-----------------|-------------|----------|--------------|----------------|------------------|
| 10/512,131      | 10/21/2004  | Unknown  | 29175        | Unknown        | Unknown          |

Title: **SEMICONDUCTOR LIGHT EMITTING ELEMENT, MANUFACTURING METHOD THEREOF, INTEGRATED SEMICONDUCTOR LIGHT EMITTING DEVICE, MANUFACTURING METHOD THEREOF, IMAGE DISPLAY DEVICE, MANUFACTURING METHOD THEREOF, ILLUMINATING DEVICE AND MANUFACTURING METHOD THEREOF**

**Payment of Fee**

(Only complete if Applicant elects to pay the fee set forth in 37 CFR 1.17(p))

- ☐ A check in the amount of \_\_\_\_\_ is attached.
- ☒ The Director is hereby authorized to charge and credit Deposit Account No. **02-1818** as described below.
- ☐ Charge the amount of \_\_\_\_\_
- ☒ Credit any overpayment.
- ☒ Charge any additional fee required.
- ☐ Payment by credit card. Form PTO-2038 is attached.

**WARNING: Information on this form may become public. Credit card information should not be included on this form. Provide credit card information and authorization on PTO-2038.**

**Certificate of Transmission by Facsimile\***

I certify that this document and authorization to charge deposit account is being facsimile transmitted to the United States Patent and Trademark Office (Fax. No. \_\_\_\_\_)

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(Date)

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Signature

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Typed or Printed Name of Person Signing Certificate

**Certificate of Mailing by First Class Mail**

I hereby certify that this correspondence is being deposited with the United States Postal Service with sufficient postage as first class mail in an envelope addressed to "Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450" [37 CFR 1.8(a)] on \_\_\_\_\_

02/18/2005

\_\_\_\_\_  
(Date)

\_\_\_\_\_  
Signature of Person Mailing Correspondence  
Heather Foster

\_\_\_\_\_  
Typed or Printed Name of Person Mailing Certificate

**\*This certificate may only be used if paying by deposit account.**

\_\_\_\_\_  
Signature

Dated: **February 18, 2005**

**Thomas C. Basso**  
Reg. No. 46,541  
Bell, Boyd & Lloyd LLC  
P.O. Box 1135  
Chicago, Illinois 60690-1135  
Telephone: (312) 807-4310

CC:

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

Applicant: Okuyama et al.  
Appl. No.: 10/512,131  
Conf. No.: Unknown  
Filed: October 21, 2004  
Title: SEMICONDUCTOR LIGHT EMITTING ELEMENT, MANUFACTURING  
METHOD THEREOF, INTEGRATED SEMICONDUCTOR LIGHT  
EMITTING DEVICE, MANUFACTURING METHOD THEREOF, IMAGE  
DISPLAY DEVICE, MANUFACTURING METHOD THEREOF,  
ILLUMINATING DEVICE AND MANUFACTURING METHOD THEREOF  
Art Unit: Unknown  
Examiner: Unknown  
Docket No.: 112857-534

Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

**SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT**

Sir:

In accordance with the provisions of 37 C.F.R. 1.56, 37 C.F.R. 1.97, and 37 C.F.R. 1.98, Applicants request that a citation and examination of the references cited below, and on the attached PTO-1449 form, be made during the course of examination of the above-identified application for United States patent. Pursuant to the Official Gazette Notice dated August 5, 2003, copies of the cited U.S. patents and patent applications are not included as this application was filed after June 30, 2003. However, copies of all other cited references are included with this form.

**U.S. PATENT DOCUMENTS**

| <u>Document No.</u> | <u>Date</u> | <u>Inventor</u> |
|---------------------|-------------|-----------------|
| 5,177,405           | 01-05-93    | Kusuda et al.   |
| 5,727,008           | 03-10-98    | Koga            |
| 5,732,098           | 03-24-98    | Nisitani        |
| 5,814,839           | 09-29-98    | Hosoba          |
| 5,828,088           | 10-27-98    | Mauk            |
| 5,981,977           | 11-09-99    | Furukawa et al. |
| 6,252,255           | 06-26-01    | Ueta et al.     |
| 6,320,209           | 11-20-01    | Hata et al.     |

**FOREIGN PATENT DOCUMENTS**

| <u>Document No.</u> | <u>Date</u> | <u>Country</u> |
|---------------------|-------------|----------------|
| 56-92577            | 07-27-81    | Japan          |
| 57-45583            | 03-15-82    | Japan          |
| 57-52071            | 03-27-82    | Japan          |
| 57-52072            | 03-27-82    | Japan          |
| 57-52073            | 03-27-82    | Japan          |
| 58-50577            | 03-25-83    | Japan          |
| 61-156780           | 07-16-86    | Japan          |
| 63-188938           | 08-04-88    | Japan          |
| 2-263668            | 10-26-90    | Japan          |
| 03-035568           | 02-15-91    | Japan          |
| 06-067044           | 03-11-94    | Japan          |
| 07-199829           | 04-08-95    | Japan          |
| 08-008217           | 01-12-96    | Japan          |
| 08-255929           | 10-01-96    | Japan          |
| 09-199419           | 07-31-97    | Japan          |
| 10-125929           | 05-05-98    | Japan          |
| 10-265297           | 10-06-98    | Japan          |
| 10-270801           | 10-09-98    | Japan          |
| 10-312971           | 11-24-98    | Japan          |
| 10-321910           | 12-04-98    | Japan          |
| 11-075019           | 03-16-99    | Japan          |
| 11-177138           | 07-02-99    | Japan          |
| 11-238687           | 08-31-99    | Japan          |
| 11-251253           | 09-17-99    | Japan          |
| 11-274568           | 10-08-99    | Japan          |
| 11-312840           | 11-09-99    | Japan          |
| 11-346004           | 12-14-99    | Japan          |
| 11-514136           | 11-30-99    | Japan          |
| 2000-068593         | 03-03-00    | Japan          |
| 2000-012976         | 01-14-00    | Japan          |



| <u>Document No.</u> | <u>Date</u> | <u>Country</u> |
|---------------------|-------------|----------------|
| 2000-150391         | 05-30-00    | Japan          |
| 2000-183451         | 06-30-00    | Japan          |
| 2000-223417         | 08-11-00    | Japan          |
| 2000-332343         | 11-30-00    | Japan          |
| 2001-085738         | 03-30-01    | Japan          |
| 2001-217503         | 08-10-01    | Japan          |
| 2002-185660         | 12-12-02    | Japan          |
| WO 97/44612         | 11-27-97    | PCT            |
| WO 02/07231         | 01-24-02    | PCT            |

### **OTHER DOCUMENTS**

Zheleva et al., "*Pendeo-epitaxy – a new approach for lateral growth of gallium nitride structures,*" MRS Internet J. Nitride Semicond. Res. 4S1, G3.38 (1999).

Kapolnek et al., "*Spatial control of InGaN luminescence by MOCVD selective epitaxy,*" Journal of Crystal Growth, 189/190 (1998) pp. 83-86.

Wang et al., "*Fabrication of nanoscale structures of InGaN by MOCVD lateral overgrowth,*" Journal of Crystal Growth 197 (1999), pp. 48-53.

Singh et al., "*Selective Area Growth of GaN Directly on (0001) Sapphire by the HVPE Technique,*" MRS Internet Journal Nitride Semiconductor Research, 3, 13 (1998), pp. 1-4.

Mao, et al., "*Defects in GaN Pyramids Grown on Si(111) Substrates by Selective Lateral Overgrowth,*" Materials Research Society Meeting in Boston, Mass. (1998) pp. 1-6.

Yang et al., "*Single-crystal GaN pyramids grown on (111)Si substrates by selective lateral overgrowth,*" Journal of Crystal Growth, Vol. 204, No. 3, (1999), pp. 270-274.

Stringfellow et al., Journal of Crystal Growth, Vol. 204, No. 3, July 11 (1999), pp. 247-418.

Applicants look forward to early and favorable consideration of this matter.

Respectfully submitted,

BELL, BOYD & LLOYD LLC

BY



Thomas C. Basso  
Reg. No. 46,541  
P.O. Box 1135  
Chicago, Illinois 60690-1135  
Phone: (312) 807-4310

Dated: February 18, 2005

|  |                               |                               |
|--|-------------------------------|-------------------------------|
| <b>INFORMATION DISCLOSURE CITATION<br/>IN AN APPLICATION</b><br>(Use several sheets if necessary)<br><br>PTO Form 1449 | Atty Docket No.<br>112857-534 | Application No.<br>10/512,131 |
|  | Applicant<br>Okuyama et al.   |                               |
|  | Filing Date<br>10/21/2004     | Group<br>Unknown              |

| U.S. PATENT DOCUMENTS |  |                 |                  |                 |       |          |                            |
|-----------------------|--|-----------------|------------------|-----------------|-------|----------|----------------------------|
| Examiner's Initials   |  | Document Number | Publication Date | Inventor        | Class | Subclass | Filing Date If Appropriate |
|                       |  | 5,177,405       | 01-05-93         | Kusuda et al.   |       |          |                            |
|                       |  | 5,727,008       | 03-10-98         | Koga            |       |          |                            |
|                       |  | 5,732,098       | 03-24-98         | Nisitani        |       |          |                            |
|                       |  | 5,814,839       | 09-29-98         | Hosoba          |       |          |                            |
|                       |  | 5,828,088       | 10-27-98         | Mauk            |       |          |                            |
|                       |  | 5,981,977       | 11-09-99         | Furukawa et al. |       |          |                            |
|                       |  | 6,252,255       | 06-26-01         | Ueta et al.     |       |          |                            |
|                       |  | 6,320,209       | 11-20-01         | Hata et al.     |       |          |                            |

| FOREIGN PATENT DOCUMENTS |  |                 |                  |         |       |          |             |    |
|--------------------------|--|-----------------|------------------|---------|-------|----------|-------------|----|
| Examiner's Initials      |  | Document Number | Publication Date | Country | Class | Subclass | Translation |    |
|                          |  |                 |                  |         |       |          | Yes         | No |
|                          |  | 56-92577        | 07-27-81         | Japan   |       |          |             |    |
|                          |  | 57-45583        | 03-15-82         | Japan   |       |          |             |    |
|                          |  | 57-52071        | 03-27-82         | Japan   |       |          |             |    |
|                          |  | 57-52072        | 03-27-82         | Japan   |       |          |             |    |
|                          |  | 57-52073        | 03-27-82         | Japan   |       |          |             |    |
|                          |  | 58-50577        | 03-25-83         | Japan   |       |          |             |    |
|                          |  | 61-156780       | 07-16-86         | Japan   |       |          |             |    |
|                          |  | 63-188938       | 08-04-88         | Japan   |       |          |             |    |
|                          |  | 2-263668        | 10-26-90         | Japan   |       |          |             |    |
|                          |  | 03-035568       | 02-15-91         | Japan   |       |          |             |    |
|                          |  | 06-067044       | 03-11-94         | Japan   |       |          |             |    |
|                          |  | 07-199829       | 04-08-95         | Japan   |       |          |             |    |
|                          |  | 08-008217       | 01-12-96         | Japan   |       |          |             |    |
|                          |  | 08-255929       | 10-01-96         | Japan   |       |          |             |    |
|                          |  | 09-199419       | 07-31-97         | Japan   |       |          |             |    |
|                          |  | 10-125929       | 05-05-98         | Japan   |       |          |             |    |
|                          |  | 10-265297       | 10-06-98         | Japan   |       |          |             |    |
|                          |  | 10-270801       | 10-09-98         | Japan   |       |          |             |    |

|  |                  |
|--|------------------|
| Examiner:  | Date Considered: |
| *Examiner: Initial if citation considered, whether or not citation is in conformance with MPEP Section 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. |                  |

|  |                               |                               |
|--|-------------------------------|-------------------------------|
| <b>INFORMATION DISCLOSURE CITATION<br/>IN AN APPLICATION</b><br>(Use several sheets if necessary)<br><br>PTO Form 1449 | Atty Docket No.<br>112857-534 | Application No.<br>10/512,131 |
|  | Applicant<br>Okuyama et al.   |                               |
|  | Filing Date<br>10/21/2004     | Group<br>Unknown              |

| FOREIGN PATENT DOCUMENTS |  |                    |                     |         |       |          |             |    |
|--------------------------|--|--------------------|---------------------|---------|-------|----------|-------------|----|
| Examiner's<br>Initials   |  | Document<br>Number | Publication<br>Date | Country | Class | Subclass | Translation |    |
|                          |  |                    |                     |         |       |          | Yes         | No |
|                          |  | 10-312971          | 11-24-98            | Japan   |       |          |             |    |
|                          |  | 10-321910          | 12-04-98            | Japan   |       |          |             |    |
|                          |  | 11-075019          | 03-16-99            | Japan   |       |          |             |    |
|                          |  | 11-177138          | 07-02-99            | Japan   |       |          |             |    |
|                          |  | 11-238687          | 08-31-99            | Japan   |       |          |             |    |
|                          |  | 11-251253          | 09-17-99            | Japan   |       |          |             |    |
|                          |  | 11-274568          | 10-08-99            | Japan   |       |          |             |    |
|                          |  | 11-312840          | 11-09-99            | Japan   |       |          |             |    |
|                          |  | 11-346004          | 12-14-99            | Japan   |       |          |             |    |
|                          |  | 11-514136          | 11-30-99            | Japan   |       |          |             |    |
|                          |  | 2000-068593        | 03-03-00            | Japan   |       |          |             |    |
|                          |  | 2000-012976        | 01-14-00            | Japan   |       |          |             |    |
|                          |  | 2000-150391        | 05-30-00            | Japan   |       |          |             |    |
|                          |  | 2000-183451        | 06-30-00            | Japan   |       |          |             |    |
|                          |  | 2000-223417        | 08-11-00            | Japan   |       |          |             |    |
|                          |  | 2000-332343        | 11-30-00            | Japan   |       |          |             |    |
|                          |  | 2001-085738        | 03-30-01            | Japan   |       |          |             |    |
|                          |  | 2001-217503        | 08-10-01            | Japan   |       |          |             |    |
|                          |  | 2002-185660        | 12-12-02            | Japan   |       |          |             |    |
|                          |  | WO 97/44612        | 11-27-97            | PCT     |       |          |             |    |
|                          |  | WO 02/07231        | 01-24-02            | PCT     |       |          |             |    |

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| *Examiner: Initial if citation considered, whether or not citation is in conformance with MPEP Section 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. |                  |

